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#### **40V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C		
40V	$0.05\Omega$ @ $V_{GS} = 10V$	7A		

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- DC-DC Converters
- Audio Output Stages
- · Relay and Solenoid Driving
- Motor Control

#### **Features**

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMN4A06GQ)

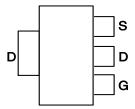
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

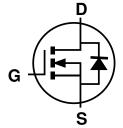




Top View



Pin Out - Top View



Equivalent Circuit

#### **Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
ZXMN4A06GTA	Standard	SOT223	1,000/Tape & Reel
ZXMN4A06GTC	Standard	SOT223	4,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- ${\it 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.}\\$

# **Marking Information**

ZXMN \* 4A06 \*

SOT223

ZXMN4A06 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 6 = 2016) WW or  $\overline{W}W$  = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	40	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 6)		7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70$ °C (Note 6)	I <sub>D</sub>	5.6	Α
		(Note 5)		5	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 7)	I <sub>DM</sub>	22	Α
Continuous Source Current (Body Diode) (Note 6)		Is	5.4	Α	
Pulsed Source Current (Body Diode) (Note 7)		I <sub>SM</sub>	22	Α	

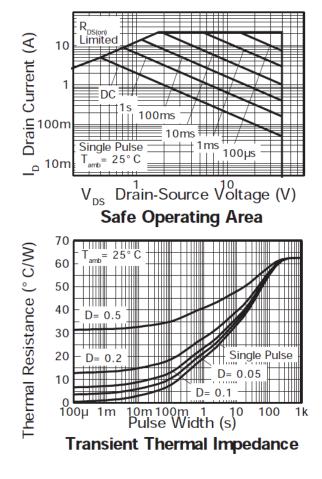
#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

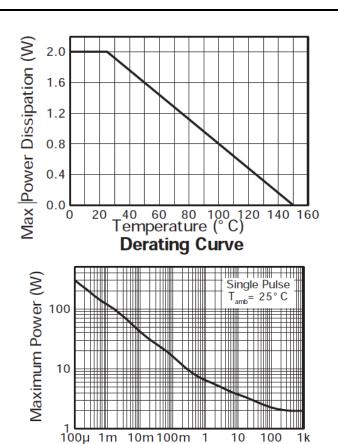
Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		2 16	W	
Linear Derating Factor	(Note 6)	- P <sub>D</sub>	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 7)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	32.2		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t  $\leq$  5 seconds.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width  $10\mu s$  pulse width limited by maximum junction temperature.

### **Thermal Characteristics**





Pulse Width (s)

Pulse Power Dissipation



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

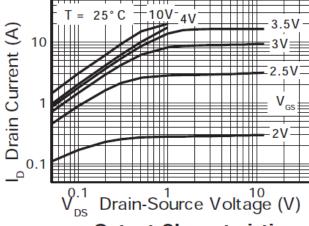
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 40V$ , $V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	1		2	٧	$I_D=250\mu A,\ V_{DS}=V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	D			0.05	Ω	$V_{GS} = 10V, I_D = 4.5A$	
Static Drain-Source On-Resistance (Note 6)	R <sub>DS(ON)</sub>	_		0.075	Ω	$V_{GS} = 4.5V, I_D = 3.2A$	
Forward Transconductance	g <sub>fs</sub>		8.7	_	S	$V_{DS} = 15V, I_D = 2.5A$	
Diode Forward Voltage (Note 8)	$V_{SD}$		0.8	0.95	V	$I_S = 2.5A$ , $V_{GS} = 0V$ , $T_J = +25$ °C	
Reverse Recovery Time (Note 9)	t <sub>RR</sub>		19.86	_	ns	$I_F = 2.5A$ , di/dt = 100A/ $\mu$ s,	
Reverse Recovery Charge (Note 9)	Q <sub>RR</sub>		16.36	_	nC	$T_J = +25$ °C	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		770	_	pF		
Output Capacitance	Coss		92	_	pF	$V_{DS} = 40V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	Crss		61	_	pF		
Total Gate Charge	Qg		18.2	_	nC	$V_{DS} = 30V$ , $V_{GS} = 10V$ , $I_D = 2.5A$ (Refer to test circuit)	
Gate-Source Charge	Q <sub>gs</sub>	_	2.1	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	4.5	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.55	_	ns	$V_{DD}$ = 30V, $V_{GS}$ = 10V $I_{D}$ = 2.5A, $R_{G} \approx 6\Omega$ (Refer to test circuit)	
Turn-On Rise Time	t <sub>r</sub>	_	4.45	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	28.61	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	7.35	_	ns		

Notes:

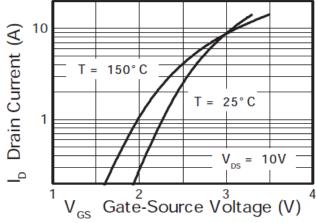
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



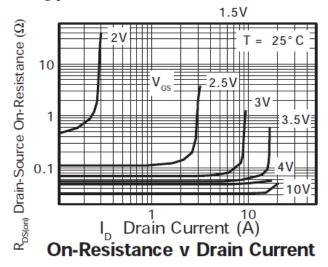
# **Typical Characteristics**

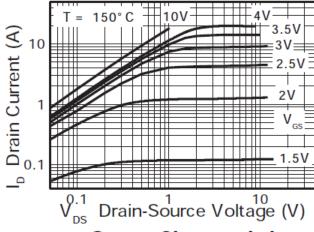


# **Output Characteristics**

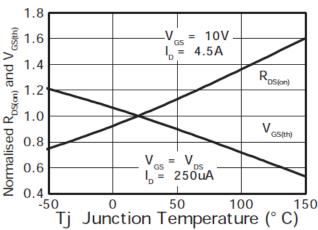


# **Typical Transfer Characteristics**

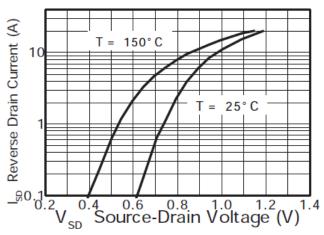




# **Output Characteristics**



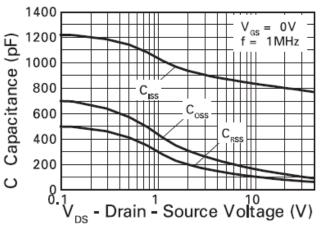
# Normalised Curves v Temperature



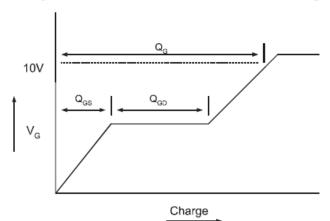
Source-Drain Diode Forward Voltage



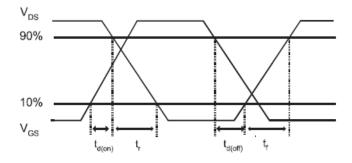
### **Typical Characteristics** (Cont.)



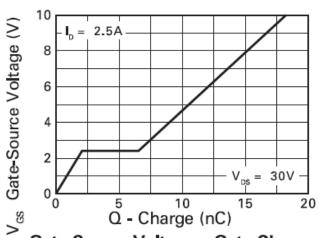
# Capacitance v Drain-Source Voltage



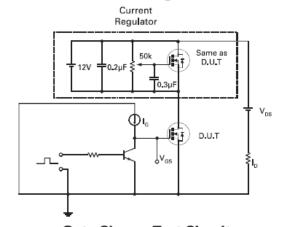
**Basic Gate Charge Waveform** 



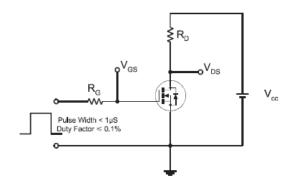
**Switching Time Waveforms** 



Gate-Source Voltage v Gate Charge



**Gate Charge Test Circuit** 

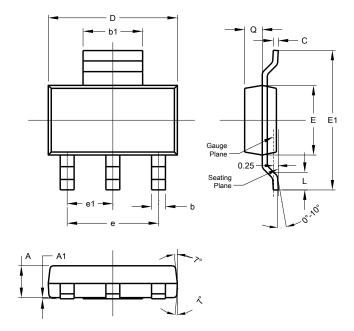


**Switching Time Test Circuit** 



# **Package Outline Dimensions**

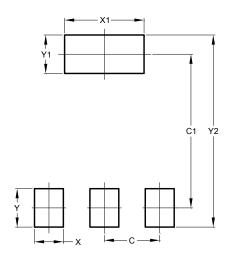
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		



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